A Theoretical Study of the Electrochemical Gate E ect in a STM -based biom olecular transistor

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A bstract

E lectroC hem ical Scanning Tunneling M icroscopy (ECSTM) is gaining popularity as a tool to implement proof-of-concept single (bio)m olecular transistor. The understanding of such systems requires a discussion of the mechanism of the electrochemical current gating, which is intimately related to the electrostatic potential distribution in the tip-substrate gap where the redox active adsorbate is placed. In this article, we derive a relation that connects the local standard potential of the redox molecule in the tunneling junction with the applied electrode potentials, and we compare it with previously proposed relations. In particular, we show that a linear dependence of the local standard potential on the applied bias does not necessarily imply a monotonous potential drop between the electrodes. In addition, we calculate the electrostatic potential distribution and the parameters entering the derived relation for ECSTM on a redox metalloprotein (A zurin from P. A eruginosa), for which experimental results exist. Finally, we give an estimate of the gating electrony when the ECSTM setup including A zurin is interpreted as a single biomolecular wet transistor, con implicit the electrochemical gating for this system.

1 Introduction

The Holy-G railofm olecular electronics¹ is the realization of working transistors based on a single molecule. In particular, to realize a eld e ect single (bio)-molecule based transistor, three di erent electrodes should surround the molecule: a source, a drain and a gate. Ideally, source and drain should exchange electrons with them olecule (i.e., they should provide the electric current) without a ecting the molecular energy levels, while gate should tune the molecular energy level (via the produced electric eld) without exchanging electrons with it. This implies that, when the gate is in plemented as a third metallic electrode, it must be microscopically close to the molecule and, at the same time, electrically isolated from it.² M eeting such requirements represents a form idable experimental task. An elegant alternative solution to the gating problem is provided by the electrochemical gate e ect,³ conveniently implemented with ElectroChemical Scanning Tunneling Microscopy (ECSTM).⁴

When standard (i.e., non electrochemical) STM is used to study single redox-active (bio)m olecule adsorbed on a solid conductive substrate, the resulting setup is close to that of a eld e ect transistor (the conductive substrate represents the source and the tip acts as the drain) but the gate electrode is lacking. In ECSTM, the STM tip and substrate are in m ersed in an ionic solution, and their potentials are controlled with a bipotentiostat w rt a reference electrode. Thanks to this bipotentiostat, ECSTM allows to control not only the potential bias between tip and substrate (tip) potential and the reference potential of the solution. In other words, in ECSTM we can modify the electrochem ical potentials of tip and substrate with respect to that of a redox molecule in solution, or, vice-versa, we can tune the energy of the molecular redox level w rt. the tip and substrate electrochem ical potentials. Since the relative position of the redox level controls them olecular conductance,

gating is eventually obtained. The features of ECSTM has been exploited by di erent groups to demonstrate electrochem ical gating, 5^{12} and thus to propose/implement proof-of-concept single molecule transistors.^{13,14}

Several theoretical works have been devoted to the study of the conduction m echanism s of redox adsorbate in ECSTM^{15{20}</sup> and, in general, to STM in water solution.^{21{24} In the present article, the focus is not on the conduction mechanism itself, but on the electrostatic potential induced by the applied electrode potentials in the tip-substrate gap and on its relations with the electrochem ical gate e ects. A fundam ental role in interpreting experiments on standard STM and molecular wires is played by the electrostatic potential distribution in the tunneling gap. It has been argued that the feature of the I (V) curve dram atically depends on the fraction of tip-substrate potential bias dropping on the m olecule.²⁵ In ECSTM, it is clear that electrostatic potential must play a relevant role too. This was recognized early,²⁶ how ever, till very recently,²⁷ not much attention has been given to the e ects of the ionic atm ospheres on the electrostatic potential distribution induced in the tip-substrate gap by the applied electrode potentials. For example, in interpreting experiments on adsorbate conduction in ECSTM, a linear relation between the fraction of the bias potential acting on a redox center and the geom etrical position of the redox center in the tunneling gap has been assumed.^{10,11} Is this picture correct for ECSTM of adsorbates? One of the aim s of the present article is to answer to this question in a speci c case that is particularly am biguous.

In addition, the feature of the electrostatic potential distribution in ECSTM are strictly related to a quantity which is fundam ental when considering ECSTM experiments as realizations of single m olecule transistors: the gating e ciency. In this article, this quantity will be estimated as a function of the system parameters.

The discussion of electrochem ical phenom ena such as those controlling gating in EC-STM may become muddled due to the use of the term potential to indicate di erent quan-

tities. In the discussion that follows we should be careful in distinguishing between these quantities: the electrostatic potential (physical dimension of an energy divided by a charge); the electrochem ical potential (physical dimension of an energy) and the electrochem potential or V (physical dimension as , but it is related to a dimension of electrochem ical potentials, divided by e, the modulus of the electron charge).

The rest of the article is organized as follows: in Sect 2 we review the basics of the gating mechanism in ECSTM, beginning with the ideal case and describing the necessary renements associated with the microscopic origin of the process; in Sect.3 we present the continuum model that we use to describe the potential in the ECSTM setup while in Sect A results are presented and discussed. In particular, a simple relation between the standard potential of the redox molecule in the gap and the applied tip/substrate potentials is derived, the electrostatic potential distribution for a protein in the tip-substrate gap⁶ is discussed and the e ciency of an ECSTM transistor based on A zurin is presented. Finally, in Sect 5 some conclusions are drawn.

2 Review of the gating mechanism

In this section, we present a short review of the electrostatic aspects of the gating mechanism. A description of the gating mechanism in the framework of ECSTM electron tunneling mechanisms can be found, e.g., in Ref28.

We start our discussion by considering an ideal case. Let us suppose that the substrate (i.e., the source in the transistor nom enclature) is grounded. Thus, all the electrochem ical potentials are naturally referred to that of the substrate, _{sub}. In other words, in posing a variation to the substrate-reference potential di erence is equivalent to change the electrochem ical potential of the reference electroche ($_{ref}$).²⁹ W hen such a variation is in posed (i.e., when $_{ref}$ is changed), the characteristic sem i-reaction of the reference electroche is

drawn out of therm odynam ic equilibrium. To recover the equilibrium, the reaction advances or retrocedes, releasing or rem oving ions from the solution. This change in the ionic balance of the solution modies sol, the electrostatic potential of the solution itself, and, in turn, the electrochem ical potential of the ions already present in solution. The new equilibrium is settled when the electrostatic potential variation of the solution $\begin{pmatrix} s_{ol} \end{pmatrix}$ is such that to have compensated for the initially imposed electrochem ical potential variaref, where e is the modulus of the electron charge (see appendix A for tions: e sol = a proof).³⁰ The molecule feels now the new sol. The energy of each molecular electronic level (in particular of the redox one, i.e., that occupied upon reduction) is thus modi ed by a quantity e sol = ref. In conclusion, if the potential di erence applied between the transistor source (i.e., the ECSTM substrate) and the gate (i.e., the reference electrode) is changed by a given quantity, then, in this ideal picture, the energy of the redox level of the molecule is changed by the same amount (times e), while the source (substrate) and drain (tip) remained constant. This modi cation of the redox energy level of the molecule w.r.t. the source (substrate) and drain (tip) level is precisely what gives origin to gating.

So far, we did not stress that while sol varies in response to a change in ref, the electrostatic potential in the substrate is xed, since such electrode is grounded. Thus, the electrostatic potential di erence between the interior of the substrate and the solution must change of $_{sol} = _{ref} = (e)$. Ideally, there is a step in the potential pro le going from the substrate to the solution, whose size is equal to the applied substrate reference potential up to an unknown but xed constant. This electrostatic potential drop is step-like only at the macroscopic scale (see Fig. 1). In fact, microscopically, the electrostatic potential drop is due to the inbalance of positive and negative ions close to the charged electrode surface, which creates a net density of charge in the solution layer neighboring the electrode.³¹ The structure of this density of charge is described by the Stem double-layer model, which extends for a few nm's (depending mainly on the ionic strength) in

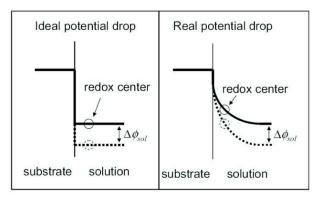


Figure 1: Schem atic representation of the electrostatic potential drop from the substrate to the solution assuming an ideal (left) or real (right) behavior. Note that when sol is changed, the electrostatic potential at the position of the redox center changes by di erent am ounts in the two cases.

the solution. W hen the redox molecule resides inside this layer (as for adsorbates) the electrostatic potential acting on the molecule (called $_{\rm m}$) is di erent from $_{\rm sol}$. Thus, the electrochem ical potential variation imposed on the gate (i.e., reference) electrode does not translate completely into the variation of $_{\rm m}$. A measure the electrochemess of the gate in controlling the molecule potential is the gate control parameter,² de ned as:

$$= \frac{\varrho_{m}}{\varrho_{V_{g}}}$$
(1)

where V_g is the potential applied to the gate. C learly, = 1 in the ideal case while 1 in the real case.

W e end this discussion by remarking that the e ects related to the incomplete screening of the electrode charge at the position of the molecule have well-known consequences in electrochem ical kinetics, where they originate the so-called Frum kin e ect.^{32,34}

In the following, we shall discuss how the electrostatic e ects of the source and drain electrodes on $_{m}$ (and thus on) can be calculated within a simple model.

3 Outline of the model

W e are not aware of calculation of electrostatic potential distribution for a m olecule (in particular, a protein) in ECSTM, although calculations for empty tunneling gap appeared very recently.²⁷ Thus, we start by considering a relatively simple m odel based on a continuum dielectric representation, for which useful relations can be promptly derived. Basically, tip and substrate are represented as perfect conductors (substrate with a planar surface, tip with a spherically curved surface),³⁵ and the adsorbate is a dielectric with a realistic shape (solvent-excluded surface). The redox center of the adsorbate is not explicitly m odeled: we simply de ne m as the electrostatic potential at the geom etrical position of such center. A s for the ionic solution surrounding the adsorbate, it is described as another dielectric while the ionic atm osphere is in plicitly accounted for by considering the linearized Poisson-Boltzm ann equation to obtain the potential in the system :

$$r (r) + {}^{2}K _{sol} = - _{0}$$
 (2)

where is the relative dielectric constant (of the solvent or the adsorbate, depending on the position) and k is the inverse screening length (equal to zero inside the adsorbate), proportional to the square root of the ionic strength I. The Helm holtz layer is taken into account by assuming that the region of solution closest to the electrodes cannot contain ions (i.e., k = 0, see appendix B). The electrostatic potential drop inside this region is thus linear. We shall not consider any specie c ion adsorption at the electrode surfaces, i.e., the concentration of ions in the Helm holtz layer is only related to their electrostatic preferences and not to other favorable interactions with the surface. We remark that a reduced dielectric constant for the water layer in the close proximity of the electrodes³² has been used as discussed in appendix B.

It is clear that the present model is quite simplied and neglects a number of e ects,

such as the non-linear character of the Poisson-Boltzm ann equation, specic ion adsorption and the accounting of the ion nite size in ion-ion interactions. Nevertheless, it catches the main physical features of the ion screening elects (also in complex systems involving biom olecules) and, more important than this, represents the framework in which corrections to the molecular redox level energy as simple as that used in Ref.19 can be derived. Re ned calculations based on the non-linear Poisson-Boltzm ann equation are given and discussed in Sect. 4.3 for a specic system.

The electrostatic potential that we consider is only due to the applied potential difference: the contributions from the intrinsic charge distribution of the redox adsorbate is already included in the factors that determ ine the standard redox potential; charging e ects of the molecule due to the electronic coupling with the electrodes are not considered here, since we focus on the electrostatic e ects due to the charged electrodes. In any case, in the fram ework of our simple, linear model, these e ects are superim possible to our results.

4 Results and Discussion

4.1 The relation between the electrostatic potential acting on the molecule and the potentials applied to the tip and the substrate

In this section, we present a general relation between the electrostatic potential acting on the molecule redox center ($_m$) and the potentials imposed on the electrodes (E_{tip} and E_{sub}). Such a relation is based on the continuum model presented above. First of all, we have to specify the electrostatic boundary conditions at the tip and substrate surfaces. We assume that the electrostatic potential at the substrate surface _{sub} is given

by $_{sub} = E_{sub} = E_{sub}^{pzc} + _{sol}$, where E_{sub} is the potential in posed to the substrate w.r.t. the reference electrode while E_{sub}^{pzc} is the potential of zero charge (pzc), i.e., the substrate potential at which the surface charge is nil. Analogous de nitions are used for the tip, yielding $_{tip} = E_{tip} = E_{tip}^{pzc} + _{sol}$. We remark that the values of E_{sub}^{pzc} and E_{tip}^{pzc} refer to a system where tip and substrate are well separated. C learly, this does not mean that, e.g., the substrate involved in a STM has a null surface charge at E_{sub}^{pzc} , since it is exposed to the electrostatic e ects of the other electrode. This is naturally taken into account by the present m odel.

Since the equation that de nes the potential in our model, eq.(2), is linear in $_{sol}$, one obtains:

$$m \quad sol = tip (tip \quad sol) + sub (sub \quad sol) = tip (E tip \quad E^{pzc}_{tip}) + sub (E sub \quad E^{pzc}_{sub}) (3)$$

Thus, the e ect of the tip and the substrate potentials on the redox center is, in our simple model, completely described by an intrinsic electrode property, E^{pzc}, and by the two coe cients tip and sub. When there is no electrostatic coupling between tip/substrate and the redox center, tip = 0; when the redox level is pinned to, e.g., the substrate then $_{sub} = 1$. Clearly, 0 $_{tip}$; $_{sub}$ 1. In addition, it is possible to proof that 1. Before giving the results of the actual calculations of $_{\rm sub}$ and $_{\rm tip}$, we tip + sub would like to draw a connection with another relation described in the literature to take into account the e ects of the tip and substrate potential on the molecular redox levels. To account for such e ects in their m ost recent m odels, 19,36 U lstrup, K uznetsov and cow orkers substitute the overpotential E $_{\rm sub}$ $E_{\rm m}^{\,0}$ (where $E_{\rm m}^{\,0}$ is the standard redox potential for the m olecule) with an elective overpotential given by (E $_{\rm sub}$ $E_{\rm m}^{\rm 0}$) $V_{\rm bias}$ with 0 ; 1. and are de ned as "the fractions of the overpotential () and bias voltage In ref.19b, () at the redox site". Following our arguments, in the ECSTM environment the e ective

redox potential $E_{m,loc}^{0}$ is given by $E_{m}^{0} + m_{sol}$, thus the elective overpotential becomes E_{sub} ($E_{m}^{0} + m_{sol}$). Equating this expression with that used in Ref.19 leads to:

$$E_{sub} (E_m^0 + I_m Sol) = (E_{sub} E_m^0) V_{bias}$$
(4)

which means:

$$_{m}$$
 sol = (1) (E_{sub} E_{m}^{0}) + V_{bias} (5)

In order to compare eq.(5) with eq.(3), we can recast the latter in the form :

$$m \quad sol = (tip + sub) E sub E_{m}^{0} + tip V_{bias} + (tip + sub) E_{m}^{0} \quad tip E_{tip}^{pzc} \quad sub E_{sub}^{pzc}$$
(6)

By comparing eq.(5) and eq.(6), one can identify = 1 ($_{tip} + _{sub}$) and $= _{tip}$. However, there are di erent terms in eq.(6) that does not appear in eq.(5), playing the role of a correction to the molecular standard redox potential E_m^0 . Not surprisingly, such a correction depends on E^{pzc} of the tip and the substrate. Notably when = 1, must be zero since = 1 implies $_{tip} = _{sub} = 0$.

We remark that $= _{tip}$ is not directly related to the drop of the applied bias in the tunneling gap, and thus does not relect the position of the redox center. In fact, $= _{tip}$ m ay be small even when the molecule is closer to the tip than to the substrate, if the ionic concentration is high enough (see below for an example). This is simply understood when one consider the peculiarity of EC STM wirt gas-phase STM. In fact, when STM is performed in gas-phase, the electrostatic potential due to the applied bias is offen (and reasonably) assumed to linearly (or at least monotonically) change between the tip and the substrate. In EC STM, the situation is very dilerent, as demonstrated in Ref.27. Suppose that tip and substrate are far enough to allow a complete screening of their respective

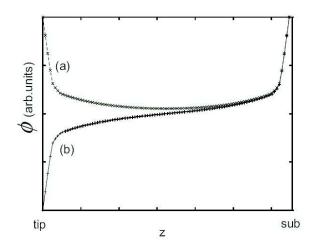


Figure 2: Electrostatic potential prodes in pure ionic solution for two di erent combinations of applied tip and substrate potentials. (a) $E_{sub} > E_{sub}^{pzc}$, $E_{tip} > E_{tip}^{pzc}$; (b) $E_{sub} > E_{sub}^{pzc}$, $E_{tip} < E_{tip}^{pzc}$. Parameters of the calculations: Ionic strength I = 0.05 M, tip-substrate distance: 40 A

surface charges by the ionic atm osphere in solution. D epending on these charges (which depend, in turn, on the imposed electrochem ical potentials), we can have four di erent situations, two of which are sketched in F ig 2 as examples. It is evident that the existence of a monotonous behavior depends on the applied potentials. W hat is important to stress here is that even when the potential drop is not linear, a linear relation between $E_{m,loc}^{0}$ (the standard potential of the molecule in the precise ECSTM gap) and the applied E_{sub} and V_{bias} is obtained from eq.(6):

$$E_{m:loc}^{0} = E_{m}^{0} + (_{tip} + _{sub}) E_{sub} E_{m}^{0} + _{tip}V_{bias} + E^{corr}$$
(7)

This means that care must be taken to assume a linear potential drop in the interpretation of ECSTM experiments only on the basis of linearity of the experimental results with the applied potentials.

In eq.(7), E $^{\rm corr}$ is a correction term that does not depend on E $_{\rm sub}$ and V $_{\rm bias}$. It depends

on E_{tip}^{pzc} and E_{sub}^{pzc} (whose experimental estimate may be dicult) but it can also collect variations of $E_{m,loc}^{0}$ that does not originate from the electrostatic electrostatic electrostatic electron with the electrodes or with other adsorbates or to the dilement properties of water con ned in the nanometric tip-substrate gap).

 $E_{m,loc}^{0}$ is an important quantity in the theories of adsorbate conduction in ECSTM, since it is related to the position of the peak of the current (or apparent height) as a function of the gate potential. Thus, eq.(7) is not only useful for theoretical considerations, but also as a tool to interpret the experimental data. Remarkably, when the ion screening is ine ective (i.e., k⁻¹ much larger than the gap size), one obtains tip + sub 1 (= 0) and $E_{sub} = E_{m,loc}^{0} = tipV_{bias} = C^{orr}$ (or $E_{tip} = E_{m,loc}^{0} = (1 - tip)V_{bias} = C^{orr}$), i.e., the relations between the potentials of the electrodes and the electrone energy of the molecular electronic levels becomes similar to that used for gas-phase (or non-ionic) STM.²⁵

4.2 Electrostatic potential distribution in ECSTM experiments on Azurin

W hen the solute is relatively large, like a protein, the electrostatic potential distribution in the tip-substrate gap is more complex than what depicted in Fig 2. In fact, the space occupied by the solute is not accessible to the ions, which cannot thus screen the potential due to the surface charges of the tip and the substrate. Thus, the potential drop inside the protein will be intermediate between two limit cases: (a) equal to that in the pure ionic solution; (b) similar to that in a non-ionic dielectric, i.e., linear as in gas-phase. One may thus wonder whether in real experiments, the potential drop is more similar to that in gas-phase or that in ionic solution without the adsorbate. To address this question, we have calculated the potential distribution with the numerical model described in appendix

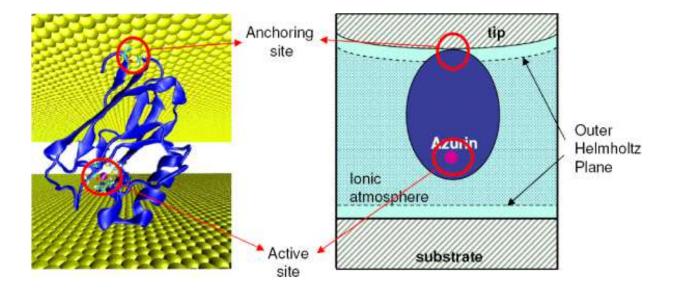


Figure 3: Pictorial representation of the Azurin orientation in the ECSTM setup exploited in Ref.6b.

B. In particular, we choose to focus on the recent experiments by Facci and coworkers.^{6b} They studied via EC STM the transport properties of tip-in mobilized A zurin, a blue-copper protein, and they demonstrate a transistor like behavior for the system. In this experiment, A zurin was anchored to the gold tip by exploiting the accessible disulde bridge between C ys3-C ys26. In our calculation, A zurin has been oriented with the major axis of inertia perpendicular to the substrate, with the S atoms of C ys3 and C ys26 at bonding distance from the tip surface. The protein redox active site (which comprises a redox active copper ion) is on the opposite side of the protein. A pictorial representation is given in Fig.3. This orientation is compatible with the experimental morphology data of A lessandrini et al.^{6b} In Fig.4 we report the potential distribution along the axis perpendicular to the electrodes and crossing the protein. To give an idea of the complexity and inhom ogeneity of the protein region. This gure con m s what we anticipated above: the potential distribution in the protein region is intermediate between the gas-phase and the pure ionic solution cases, and it is closer, in the present case, to that of a pure ionic solution. In particular,

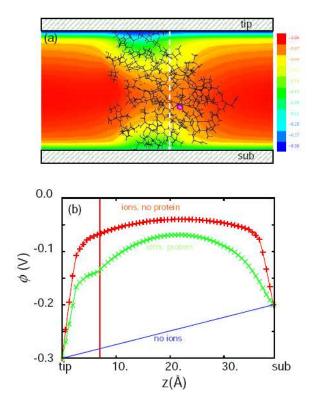


Figure 4: Potential distribution for tip-immobilized A zurin in ECSTM. (a) Cobr-code gures of the potential on a planar surface perpendicular to the electrodes surfaces. (b) E lectrostatic potential along the axis perpendicular to the electrodes and crossing the protein (dashed white line in panel (a)). For comparison, the electrostatic potential calculated in ionic solution without the protein ("ions, no protein") and for an hom ogeneous dielectric lling the space between the electrode ("no ions") are given. In (b), A zurin occupies the z region on the right of the vertical red line. Param eters of the calculation: $E_{tip} = 0.3 V + E_{tip}^{pzc}$, $E_{sub} = 0.2 V + E_{sub}^{pzc}$ (thus $V_{bias} = 0.1 V$), ionic strength I = 0.05 M, tip-substrate distance: 40 A, tip curvature radius: 1.

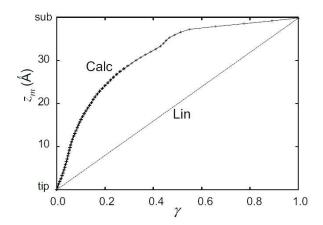


Figure 5: Position of the redox center in the tip-substrate gap (z_m) , estimated on the basis of the $=_{tip}$ value. "Calc" refers to our electrostatic calculations, "Lin" refers to a simple linear interpolation. Parameters for the calculation: ionic strength I = 0:05 M, tip-substrate distance: 40 A, tip curvature radius: 1.

we numerically show that the STM -like picture (linear potential drop between the tip and the substrate) is inappropriate to describe the potential drop in ECSTM even for a large ion-excluding adsorbate. These results also suggest that the correlation between the geom etrical position of the redox center and the potential acting on it is not straightforward. To better circum stantiate this point, we have taken the hypothetical point of view of som eone whom easured the $=_{tip}$ coe cient from an experiment (e.g., tting the current as a function of the potentials E_{sub} and V_{bias}), and who wants to use this quantity to estimate the geometrical position of the redox center in the tunneling gap (named z_m). If one assumes that V_{bias} drops linearly, the position z_m will simply be given by $z_m =$

 $_{gap}$, where l_{gap} is the gap length (i.e., the tip-substrate distance). We can compare this prediction with what can be obtained by our electrostatic calculations (these calculations give (z_m) , which can be inverted to yield z_m ()). The comparison is performed in Fig. 5. As it can be seen, the di erences can be substantial, and the redox site can be m isplaced by the linear interpolation up to 16 A, which is the 40% of the tip-substrate gap size. It is also evident that the linear interpolation results always place the redox center closer to

the tip than what it really is.

4.3 E ects of non-linearity in the Poisson-Boltzm ann equation on the potential distribution

As mentioned above, the relations and the results presented in Sects. 4.1 and 4.2 relay, am ong other assumptions, on the linearization of the Poisson-Boltzm ann equation. Due to the potential range (0.2-0.3V) and ionic strength (0.05M) considered, this assumption needs to be check. In the next section, we will show that experim ental results for A zurin are indeed linear in the applied potentials, indicating that non-linear e ects in the real system should be small. Nevertheless, as a consistency check of the model, we have perform ed som e calculations with the non-linear Poisson-Boltzm ann equation to give an estimate of the importance of non-linear e ects for the studied system. First, let us note that in principle, when the assumption of linearity is removed, we cannot consider separately the potential due to the intrinsic density of charge of A zurin and that due to the charged electrode surfaces. However, the total charge of A zurin at neutral pH is very sm all (0 or -1, depending on the oxidation state of Cu),³⁷ and electrostatic potential calculations show s that the molecule produces a potential in solution smaller than $k_B T$, that is well described by the linearized PB equation. Thus, to give an estimate of the elects of non-linearity we have focused on the potential generated by the charged electrodes alone. In particular, we have repeated the 3D calculations leading to Fig.4 by exploiting the non-linear PB equation. Results are presented in Fig.6. As it can be seen, the general appearence of the two gures is very similar, pointing to the fact that the linearized Poisson-Boltzm ann equation correctly catches the main features of the potential distribution. The color-coded potential distributions of the two panels (a) can be hardly distinguished. Note in particular that the relative behavior of the protein vs the ionic solution potential drop is the same in

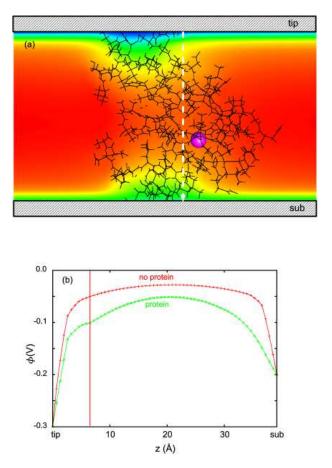


Figure 6: Potential distribution for tip-imm obilized A zurin in ECSTM calculated from the non-linear Poisson-Boltzm ann equation. (a) Color-code gures of the potential on a planar surface perpendicular to the electrodes surfaces (the color scale is the same as in Fig.4. (b) E lectrostatic potential along the axis perpendicular to the electrodes and crossing the protein (dashed white line in panel (a)). The electrostatic potential calculated in ionic solution without the protein ("no protein") is also given.

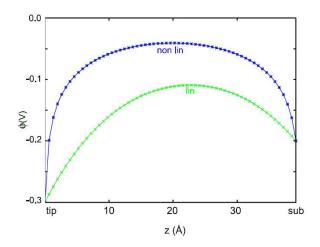


Figure 7: Electrostatic potential pro le in the tunneling gap calculated in ionic solution without the protein and neglecting the Helm holtz layer elects. "lin" refers to the potential obtained from the linearized PB equation while "non-lin" refers to the non-linear PB results.

the two gures. In panels (b), the most evident di erence is in the region between 0 and 7 A, outside the protein. On the absolute potential scales, a di erence of 15-20 mV (5 10% of the applied potentials) between the linear and the non-linear calculations is obtained on the the precise values of the potential plateau reached in the middle of the gap. The overall agreement between Fig.4 and Fig.6 can be explained by noting that most of the potential drop takes place in the Helm holtz layers that, being free from ions, behaves similarly in the linear and non-linear cases. Such an idea is supported by calculations that we performed for the empty gap by neglecting the existence of the Helm holtz layers. The results of such calculations are reported in Fig.7, where the linearized and the non-linearized PB potential drops are plotted together. As it can be seen, linearization is a much worse assumption in this case, leading to larger discrepancies between the potential pro-les.

4.4 Comparison with experimental results

C om paring the theoretical predictions reported in this article with existing experimental results is not an easy task. In fact, the experim ental i (E sub; V bias) curve depends on other parameters beside $_{\rm sub}$, $_{\rm tip}$ and $E^{\rm corr}$ that appear in eq.(7), such as the reorganization energy and the transfer integrals of the electrodem olecule electron transfer reaction. In principle, to extract all these quantities one can assume a theoretical relation $i(E_{sub}; V_{bias})$ and then adjust the parameters entering such a relation (_{sub}, _{tip}, etc.) to reproduce the experimental results. However, such a multidimensional tis not straightforward (dierent sets of parameters can give similar tting quality). Moreover, dierent mechanisms have been proposed to explain the conduction of redox-active molecules,^{15,18,19} yielding di erent relations and thus di erent tted param eters. Nevertheless, we have exploited the experin ental data of A lessandrini et al.^{6b} to extract one quantity that can be compared with our theoretical calculations. We have chosen this experiment among the few available ones for a number of reasons: (a) the ionic strength is not too high (0.05M), which improves the quality of some of the model approximations (e.g., linearization of Poisson-Boltzmann equation); (b) it is one of the few single-m olecule ECSTM experiments in which the current as a function of the substrate potential is collected for several di erent bias potentials; (c) it is the system where the non-linear nature of the potential bias drop is less obvious, since the ion screening is ine ective inside the protein and the ionic strength is relatively low; (d) the electronic couplings of the electrodes with the redox center is small, thus justifying the neglecting of electrostatic potential changes due to the elects of the lowing current on the molecular density of charge; (e) the con guration of the molecule with respect to the electrode is relatively well characterized, since azurin has only one chem isorption site available for Au (the Cys3-Cys26 solvent exposed disulphide bridge), and it is a quite rigid protein; (f) the size of the tip-substrate gap is, very likely, comparable to the molecular size (4 nm) and thus relatively large. Hence, ions concentration in the gap should not be

a ected by steric exclusion phenom ena.27

The results of R ef. 6b are curves i (E $_{tip}$) at di erent values of V $_{bias}$. Each i (E $_{tip}$) curve has a maximum for a given value of E $_{tip}$, called E $_{tip}^{max}$. Correspondingly, we can de ne E $_{sub}^{max}$, which is simply given by E_{tip}^{max} V_{bias}, and E_{avg}^{max} as $(E_{tip}^{max} + E_{sub}^{max})=2$. E_{avg}^{max} represents the mid-point between the potential of the tip and that of the substrate and, in di erent theories proposed to explain the conduction of adsorbate, it is directly related to E_{m}^{0} , i.e. R ef 20 and references therein). In addition, it does not privilege any of the two electrodes, and we shall use it for our theory-experim ent com parison. Extracting the value of E $_{tip}^{max}$ per each value of V_{bias} in the experiment, we end up with an experimental E_{avg}^{max} vs V_{bias} curve. On the other hand, from eq.(7) it is possible to derive a theoretical relation E_{avq}^{max} (V_{bias}) that can be used to t the experimental E_{avg}^{max} vs V_{bias} trend by using tip and sub as adjustable parameters. The quality of the t w ill be a measure of the validity of eq.(7), and thus of the linearization of the Poisson-Boltzm ann equation, while the tted values of $_{
m sub}$ and tip will be compared with the estimates based on our num erical model. To derive such a theoretical equation, we need a relation between $E_{m,loc}^{0}$ and E_{avg}^{max} . The sequential two-step model (the most likely mechanism for the experiments in Ref. 6b, see also 20) predicts $E_{m,loc}^{0} = E_{avg}^{max}$.²⁰ Introducing such a relation in eq.(7) leads to the E_{avg}^{max} (V_{bias}) expression that we were looking for:

$$E_{avg}^{max} = \frac{1}{2} \frac{tip}{1} \frac{sub}{tip} V_{bias} + E_m^0 + \frac{E_m^{corr}}{1} \frac{tip}{tip} sub}$$
(8)

Fitting the data of Ref.6b, we obtained that the experimental relation between E_{avg}^{max} and V_{bias} is indeed linear as predicted by eq.(8) (regression coecient R=0.95) and that the slope $(t_{ip} s_{ub})=2(1 t_{ip} s_{ub})$ is -0.12. From our electrostatic calculations, we found sub = 0.26 and $t_{ip} = 0.13$, yielding $(t_{ip} s_{ub})=2(1 t_{ip} s_{ub}) = 0.11$, in good agreement with the experiment. Unfortunately, the intercept of eq.(8) depends on E^{corr} ,

which cannot be directly derived by our simple num erical model.

C learly, this theory-experiment comparison is quite limited and involves some assumptions (such as the choice of the conduction mechanism). However, we can at least say that available experiments seem not to contradict our predictions. We hope that our results may stimulate further experiments in this eld.

O ther experiments on A zurin,¹¹ which employed dierent ECSTM geometries, cannot be treated with the same procedure used for the data of Ref. 6 since they do not measure currents but only changes in apparent heights. In addition, they do not explore the $V_{\rm bias}$ dependence of the results.

4.5 Quantifying the gating e ciency for the Azurin-based EC – STM transistor

We now pass to the discussion of the gating e ciency for A zurin in ECSTM. We have already mentioned the gate control parameter , which is a synthetic way to express the gating e ciency in a molecular Field E ect Transistor (FET)-like geometry. When = 1, all the potential applied to the gate is felt by the molecule; vice-versa when = 0 the gate is not able to modify the redox energy level. When ECSTM is seen as a FET, we can identify the potential of the gate V_g in eq.(1) with that of the reference electrode, measured w rt the grounded electrode (the source), meaning that $V_g = (ref sub)=(e)$. Since E_{sub} is de ned above as the potential di erence between the substrate and the reference electrode, and the substrate electrochem ical potential is xed (we recall that the substrate is grounded), we can write $E_{sub} = V_g$. Thus, $E_{tip} = E_{sub} + V_{bias} = V_g + V_{bias}$. In addition, we have noted above that $e_{sol} = ref$, which means that the potential of the solution sol di eres from V_g by a xed but unknown constant c (i.e., sol = $V_g + c$). Substituting these relations in eq.(3), one obtains:

$$m = C + V_g + tip (V_g + V_{bias} E_{tip}^{pzc}) + sub (V_g E_{sub}^{pzc})$$
(9)

can be easily derived from eq.(9):

$$= \frac{\varrho_{m}}{\varrho_{V_{g}}} = 1 \quad (t_{tip} + s_{ub})$$
(10)

The meaning of eq.(10) is clear: when the redox center does not feel the surface charge of tip and substrate (i.e., $_{tip} = _{sub} = 0$), the gating works ideally (= 1); on the contrary, if the molecule is a ected by the tip and/or the substrate charge the gating e ciency is reduced (0 < < 1). Remarkably, the value of also a ects the position of the peak in the tunneling current as a function of the gate potential. In fact, the peak position is related to the local standard potential of the adsorbate, $E_{m,loc}^{0}$, which depends on via tip and substrate dby eq.(7). For example, in the sequential two-step model the substrate potential giving the current maximum, E_{sub}^{max} , satis es $E_{sub}^{max} + V_{bias}=2$ $E_{m,loc}^{0}$.²⁰ Introducing such condition in eq.(7) one obtains:

$$E_{sub}^{max} = E_{m}^{0} + \frac{tip}{2} V_{bias} + \frac{E^{corr}}{2}$$
(11)

W hen = 1 (i.e., $_{tip} = _{sub} = 0$), then $E_{sub}^{max} = E_m^0 + E_m^{corr} V_{bias} = 2$, while < 1 can either increase or decrease E_{sub}^{max} depending of the sign of E_m^{corr} and the value of $_{tip}$.

Since an elective screening of the electrode surface charges is needed to have high values of , one expects that an important parameters for determining is the ionic strength I of the solution. In fact, the higher the ionic strength, the smaller is the screening length k⁻¹. To estimate (at least in the framework of our simple, linearized model) the dependence of on k⁻¹, we have performed calculations on the A zurin-based biotransistor, whose results

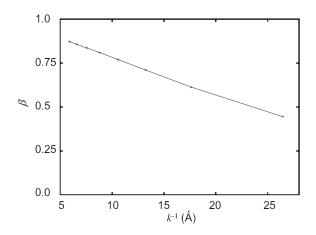


Figure 8: The gating e ciency for an Azurin-based transistor as a function of the screening length k 1 . The tip-substrate distance is 40 A

are depicted in Fig.8. A lthough the values of indicate that the azurin-based transistor is not working ideally, they are high enough to con m that the ECSTM approach to gating is convincing even in the am biguous situation of a protein. In particular, the values of range from 0.45 to 0.85 for k⁻¹ between 25 A and 5A. The value of for the ionic strength used in the experiment of Ref. 6b (I= 0.05 M) is around 0.6, which is coherent with the observed gating behavior. In the light of the results of Fig. 8, we can de ne k⁻¹, the typical length over which the e ects of a charge in ionic solution are screened, as an e ective gate size in ECSTM. In fact, 1 when k⁻¹ << l_{gap} and 0 when k⁻¹ >> l_{gap}, as expected. Rem arkably, we also found that = 0.5 when k⁻¹ 20A l_{gap}=2 (the tip-substrate distance l_{gap} is 40 A, which is in turn related to the protein size).

5 Conclusion

To sum marize the contents of this article, we have discussed how the gating mechanism acts in a wet transistor based on ECSTM and we have used a simple computationalm odel to give num erical estimates of the relevant quantities for a bio-transistor based on A zurin. In particular:

W e argued that the potential drop (due to the applied bias) in ECSTM of large adsorbates is not m onotonic and linear, in analogy to what happens for empty ECSTM gaps.²⁷

We showed that the potentials applied to tip and substrate can indeed a ect the redox energy level of the probed biom olecule, when realistic parameters for the system are used.

W e dem onstrated that, in the sim plifying fram ework of a linearized Poisson-Boltzm ann model, the variation of the redox energy level is indeed proportional to the tip and substrate potentials, as exploited in models to explain ECSTM 19 W e have emphasized that this proportionality does not generally imply a spatially linear potential drop between tip an substrate, an assumption that may lead to misinterpretations of the experimental results. In addition, we have considered the role of pzc potentials in a straightforward way.

We have quantized the gating control parameter for the protein bio-transistor, an in portant quantity that expresses the gating ending ending as a function of the parameters of the system .

We have identified a quantity (the screening length k 1) that acts as an elective gate size in ECSTM .

We remark again that the computationalm odel is quite rough, and to obtain more precise estimates, more complex models must be used. However, since this is, to the best of our knowledge, the rst study on the potentials in these bio-ECSTM systems, the simplem odel used allowed a clear indication of trends and gave insights into the basic physics of the system.

A cknow ledgm ents The author thanks Andrea A lessandrini and Paolo Facci for the useful discussions and the reading of a previous version of the manuscript.

A Proof that e sol = ref

Let us suppose that the half-reaction of the reference electrode is in the general form :

$$\sum_{j} J^{c_j} ne_{elec} = 0$$
 (12)

where we have used the convention that stoichiom etric coe cient $_{j}$ are negative for reactant and positive for product, while c_{j} is the charge of the species J and n is the number of exchanged electrons. Charge balance of eq.(12) in plies:

while therm odynam ic equilibrium is expressed by:

$$X_{jj} n_{ref} = 0$$
(14)

where $_{j}$ is the electrochem ical potential of the species J and $_{ref}$ is the electrochem ical potential of the electrons in the reference electrode. When $_{ref}$ is changed to $_{ref}^{0}$, with $_{ref} = _{ref}^{0}$ $_{ref}$, the reaction (12) will advance or retroced, modifying the concentrations of J by negligible quantities but creating a macroscopic variation of $_{sol}$, the electrostatic potential of the solution. If we call $_{sol}$ such a variation, elementary therm odynamics gives:

The condition for the new therm odynamics equilibrium is given by P_{jjj}^{0} n $_{ref}^{0} = 0$. Taking the di erence between this equation and eq.(14), one obtains:

$$X_{j j n ref} = 0$$
(16)

U sing the expression of $_{i}$ as given in eq.(15), eq.(16) becomes:

$$e \underset{j}{\text{sol}} c_{j} n \underset{\text{ref}}{} = 0$$
(17)

Exploiting the charge balance eq.(13), we nally get:

$$e_{sol} = _{ref}$$
(18)

B Num erical M ethods

In the article, we have brie y described the model used to calculate the electrostatic potential distribution (and thus tip, sub and) for A zurin in the ECSTM setup. Here, technical details on these calculations will be given. We recall that we are using a continuum model to describe the system : the electrodes (tip and substrate) are assumed to be perfect conductors (the substrate is at, the tip has a spherical curvature), the protein is a complex-shaped dielectric that cannot be penetrated by ions and the ionic solution is a dielectric that Ils all the space left empty by the other components of the system. In particular, the presence of an ionic atm osphere is taken into account by using the linearized Poisson-Boltzm an equation eq.(2), which reduces to the Poisson one inside the protein. Thus, to calculate the electrostatic potential distribution in the system , we have to solve these equations with the boundary conditions given by the applied tip and substrate potentials. The num erical procedure used to perform such a task is the Finite D i erence

(FD) method. Basically, the di erential Poisson-Boltzmann equation is discretized on a regular grid, using standard expressions for the Laplacian (correct to the third order in the grid spacing, for the present article). Such a discretization translates the di erential Poisson Boltzmann equation in a linear problem of the kind A x = b, where the known term b is given by the electrostatic potential at the boundary of the considered system, the unknown x is the potential in the interior of the system and the coe cient matrix A depends on the dielectric constant and the inverse screening length k. The boundary condition between the protein and the solution can be directly taken into account in the resolution of the problem by de ning a position-dependent dielectric constant and inverse screening length in such a way that (r) = pro and k(r) = 0 if r 2 protein, and (r) = sol $k(r) = k_{sol}$ if $r \neq protein$. We have de ned the protein region as the interior part of the solvent-excluded surface of the protein. In particular, in all the simulations we have used pro = 4, a typical value for electrostatic calculations in protein m edia. The step change of properties at the protein boundary is incompatible with the FD approach, where quantities should not vary too much on the grid spacing. For this reason, we smeared (r) and k(r)at the boundaries by interpolating between the protein and the solution values of and k. The sm earing is obtained via the arctan function.

To improve the description of the solution regions close to the electrodes (i.e., the Helm holtz layers), for the region outside the protein we have assumed that:

$$(\mathbf{r}) = 6:0 \quad \mathbf{k} \ (\mathbf{r}) = 0 \quad \text{for} \quad \mathbf{d} < 2:\mathbf{S}\mathbf{A}$$
$$(\mathbf{r}) = 30:0 \quad \mathbf{k} \ (\mathbf{r}) = \mathbf{k}_{sol} \quad \text{for} \quad 2:\mathbf{S}\mathbf{A} < \mathbf{d} < 4:\mathbf{S}\mathbf{A}$$
$$(\mathbf{r}) = 78:\mathbf{3}9 \quad \mathbf{k} \ (\mathbf{r}) = \mathbf{k}_{sol} \quad \text{for} \quad 2:\mathbf{S}\mathbf{A} < \mathbf{d} < 4:\mathbf{S}\mathbf{A}$$
(19)

where d is the distance of the point r from the surface of the closest electrode. The distances and the dielectric constants are typical values used to reproduce the experimental

capacitance of double layers.³⁸ They are rem in iscences, in the fram ework of our very simple m odel, of the properties of the inner (d 2:8 A) and outer (d 4:8 A) Helm holtz planes. Again, at the boundaries between the various d regions, and k have been sm oothly interpolated.

At this point, we would like to discuss which boundary conditions we used for the electrostatic potential. We have discretized a rectangular box having the substrate and the tip surfaces as basis, and containing the protein at the center. On tip and substrate surfaces, we imposed a value of the substrate potential given by substrate $E_{sub=tip}^{pzc}$, taking sol = 0 in eq.(2). On the lateral faces we imposed the potential distribution proper for the system without the protein. We enlarged the box until the potential results in the protein region did not depend on the box size anym ore.

We remark that the potential distribution for any combination of $_{sub}$ and $_{tip}$ values can be obtained with just two calculations: one with $_{sub} = 1$ and $_{tip} = 0$ and the other with $_{sub} = 0$ and $_{tip} = 0$. Since the electrostatic problem that we solved is linear, the potential distribution for any other value of $_{sub}$ and $_{tip}$ can be obtained by linearly combining the results of these calculations.

Finally, we give some details on the numerical resolution of the non-linear PB equation, necessary to obtain the results presented in Sect.4.3. An iterative procedure starting from the linearized solution were employed. At each step, the non-linear terms of the PB equation were Taylor-expanded to the rst order in the potential, using the potential obtained in the previous step as the center of the expansion. The so-obtained linear equation is numerically solved and a new iteration is started. The procedure was stopped when the potential values changed less than a given relative threshold (10⁵). To test the correctness of the results, we checked that the potential pro-less presented in Ref.27 were reproduced by our code.

W e conclude this section by m entioning that the m odel described here has been im -

plemented in an home-made FORTRAN 90 code, and that the solution of the numerical FD problem has been obtained by standard numerical techniques (bi-conjugate gradient algorithm). Typical parameters used in the calculations are: a grid space of 0:65 A, 300 grid points in the x and y directions (parallel to the electrode surface) and 60-80 grid points in the z direction (perpendicular to the electrode surface).

References

- [1] A.N itzan, and M.A.Ratner, Science 300, 1384 (2003).
- [2] P.Damle, T.Rakshit, M.Paulsson, and S.Datta, IEEE Trans. Nanotech. 1, 145 (2002).
- [3] (a) M. Kruger, M.R. Buitelaar, T. Nussbaumer, C. Schonenberger, and L. Forro
 Appl. Phys. Lett. 78, 1291 (2001); (b) S. Rosenblatt, Y. Yaishi, J. Park, J. Gore,
 V. Sazonova, and P.L.McEuen, Nano Lett. 2, 869 (2002).
- [4] H. Siegenthaler, in: Scanning Tunneling Microscopy II, edited by R.W iesendager, and H.-J.Guntherodt (Springer, Berlin, 1995), p.7
- [5] N J.Tao Phys.Rev.Lett. 76, 4066 (1996).
- [6] (a) A.A. Lessandrini, M.G. erunda, G.W. Canters, M. Ph.Verbeet, and P.Facci, Chem.
 Phys. Lett. 376, 625 (2003); (b) A.A. Lessandrini, M. Salemo, S. Frabboni, and P.
 Facci, Appl. Phys. Lett. 86, 133902 (2005).
- [7] W. Haiss, H. van Zalinge, S.J. Higgins, D. Bethell, H. Horbenreich, D.J. Schi rin, and R.J. Nichols, J. Am. Chem. Soc. 125, 15294 (2003).
- [8] F. Chen, J. He, C. Nuckolls, R. Tucker, JE. K lare, and S. Lindsay, Nano Lett. 5, 503 (2005).

- [9] B. Xu, X. Xiao, X. Yang, L. Zang, and N.J. Tao, J. Am. Chem. Soc. 127, 2386 (2005).
- [10] T.Albrecht, A.Guckian, J.Ulstrup, and J.G. Vos, Nano Lett. 5, 1451 (2005).
- [11] Q. Chi, O. Farver, and J. Ulstrup, Proc. Natl. A cad. Sci. 102, 16203 (2005).
- [12] Z.Li, B.Han, G.Meszaros, I.Pobelov, Th.W and low ski, A.Blaszczyk, and M.Mayor, Faraday Discuss. 131, 121 (2006).
- [13] A.M. Kuznetsov, and J.Ulstrup, J.Chem. Phys. 116, 2149 (2002).
- [14] A.M. Kuznetsov, and J.Ulstrup, J.Electroanal.Chem 564, 209 (2004).
- [15] W .Schm ickler, Surf. Sci. 295, 430 (1993).
- [16] W .Schmickler and C.Widrig, J.Electroanal.Chem. 336, 213 (1992).
- [17] E.P.Friis, Y.I.Kharkats, A.M.Kuznetsov and J.Ulstrup, J.Phys.Chem.A 102, 7851 (1998).
- [18] A.M.Kuznetsov and W.Schmickler, Chem. Phys. 282, 371 (2002).
- [19] (a) J. Zhang, Q. Chi, A.M. Kuznetsov, A.G. Hansen, H.W. ackerbath, H.E.M. Christensen, J.E.T. Andersen, and J.U. Istrup, J. Phys. Chem. B 106, 1131 (2002); (b) J. Zhang, Q. Chi, T. A. Ibrecht, A.M. Kuznetsov, M. G. rubb, A.G. Hansen, H.W. ackerbath, A.C. W. elinder, and J.U. Istrup, E. Iectrochim. Acta 50, 3143 (2005).
- [20] A.Alessandrini, S.Comi, and P.Facci, Phys.Chem.Chem.Phys.8, 4383 (2006).
- [21] W .Schm ickler, Surf. Sci. 335, 216 (1995)
- [22] A.Mosyak, A.Nitzan, and R.Koslo, J.Chem. Phys. 104, 1549 (1996).

- [23] U.Peskin, A.Edlund, and I.BarOn, J.Chem. Phys. 112, 3220 (2000).
- [24] M.Galperin, A.Nitzan, and I.Benjamin, J.Phys.Chem. A 106, 10790 (2002).
- [25] S.Datta, S.Tian, R.Hong, R.Reifenberger, J.Henderson, and C.P.Kubiak, Phys. Rev.Lett. 79, 2530 (1997).
- [26] W. Schmickler in: Nanoscale Probes of the Solid Liquid Interface, edited by A.A. Gewith and H. Siegenthaler, Nato Series E, vol. 288 (Kluwerth, Dordrecht, 1995).
- [27] (a) A A . Komyshev, and A . M . Kuznetsov, E lectrochem . Comm . 8, 679 (2006); (b)
 A A . Komyshev, A M . Kuznetsov, and J. U lstrup, Proc. Natl. Acc. Sci. 103, 6799 (2006); (c) A A . Komyshev, and A . M . Kuznetsov, Chem PhysChem 7, 1036 (2006).
- [28] A M. Kuznetsov, and J. Ulstrup, J. Phys. Chem. A. 104, 11531 (2000).
- [29] We remark that experimental ECSTM setups usually have a counter electrode in addition to the reference one. The main aim of the counter electrode is to avoid currents to ow in the reference electrode during measurements, since this can alter the reference electrode potential. We shall not deal with such a complication here, since our discussion is focused on electrostatic electrostatic electrostate to current owing.
- [30] Note that the quantity of released/captured ions needed to recover the equilibrium is very small, negligible wirt the ionic concentration already present in solution. Thus, the change in the electrochem ical potential directly induced by the variation in the species concentrations, notwithstanding electrostatic electric, is very small (non-polarizable electrode). To give an estimate of concentration changes, let us consider a spherical container for the ionic solution, having radius R = 10 cm. If the applied voltage changes by 1 V, the charge Q that should be released in solution is 4 $_{0}R$. In

the specic example, Q = 11 pC, which means 0.11 fm ol of a monovalent ion and a nom inal concentration variation of 26 aM !

- [31] For the sake of completeness, we should add that the electrode-solution potential drop also has other components:³² one is due to the ordered dipole layer form ed by the water molecule on the electrode surface, the other is related to the electronic structure of the electrode surface itself.³³ However, unless the redox center is really close to the electrode (2–3 A) these potential drops do not signi cantly contribute to the di erence between the electrostatic potential acting on the molecule and in the solution bulk.
- [32] J. O'M. Bockris, A.K.N. Reddy, and M. Gamboa-Aldeco, Modern Electrochemistry 2A, 2nd ed. (Kluwer Academic, New York, 2000).
- [33] W .Schmidkler, Chem.Rev.96, 3177 (1996).
- [34] A.J. Bard, and L.R. Faulkner Electrochem ical M ethods, 2nd ed. (W iley: New York, 2001).
- [35] A ctually, we have found that when reasonable values for the tip curvature radius are used, the results are not very di erent from those with a planar tip. Thus, all the following calculations have been done with a planar tip (i.e., in nite curvature radius).
- [36] J. Zhang, A. M. Kuznetsov, and J. Ulstrup, J. Electroan. Chem. 541, 133 (2003).
- [37] F.DeRienzo, R.R.Gabdouline, M.C.Menziani, and R.C.Wade, Protein Sci., 9, 1439 (2000).
- [38] C.H.Hamann, A.Hamnett, and W.Vielstich, Electrochemistry (Wiley-VCH, Weinheim, 1998).